

ABSTRACT

A semiconductor structure and a manufacturing method therefor. The semiconductor structure includes: a first substrate and a semiconductor device located in the first substrate; a first conductive pad connected to multiple semiconductor devices; multiple second
5 conductive pads, at least one of the first conductive pads and at least one of the second conductive pads being electrically connected through a first conductive interconnection structure extending in a direction perpendicular to the first substrate; and a filling layer filled in the outer periphery of each of the first conductive pads, the first conductive interconnection structure, and each of the second conductive pads, where the first conductive interconnection
10 structure has a surface buried by a filling layer between adjacent second conductive pads. The semiconductor structure is at least conducive to improving electrical performance.

[Fig. 1]